

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT404 (D2PAK) surface mountable plastic package intended for use in circuits where very high blocking voltage, high static and dynamic  $dV/dt$  and high  $dI/dt$  can occur. This "series C" triac will commute the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by  $dV/dt$
- Less sensitive gate for high noise immunity
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Triggering in three quadrants only
- Very high voltage capability

## 3. Applications

- Compressor starting controls
- General purpose motor control
- Reversing induction motor controls e.g. vertical axis washing machines

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	1000	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 102\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	8	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	65	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	-	72	A
$T_j$	junction temperature		-	-	125	°C
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	2	6	35	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	2	13	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	2	23	35	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	20	50	mA
$V_T$	on-state voltage	$I_T = 10\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>	-	1.3	1.65	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 670\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	1000	4000	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 8\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; snubberless condition; gate open circuit; <a href="#">Fig. 12</a>	12	32	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

## 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA208B-1000C	TO263	BTA208B-1000C,118	Reel	800	TO263N (N)	26-Sep-2016
					TO263P (P)	12-Jun-2023

## 7. Marking

Table 4. Marking codes

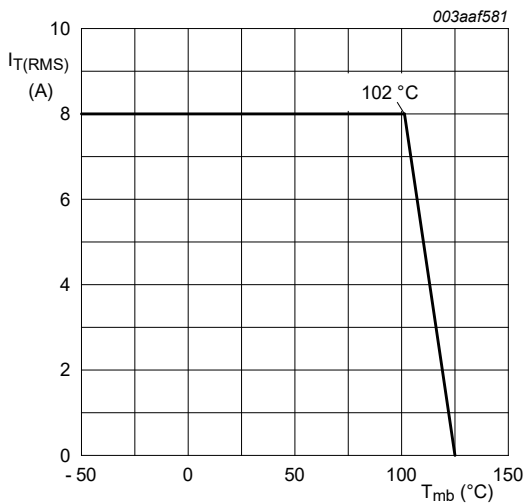
Type number	Marking codes	
	Assembly factory: N	Assembly factory: P
BTA208B-1000C	BTA208B 1000C PJNxxxx xx	BTA208B 1000C PJPxxxx xx

## 8. Limiting values

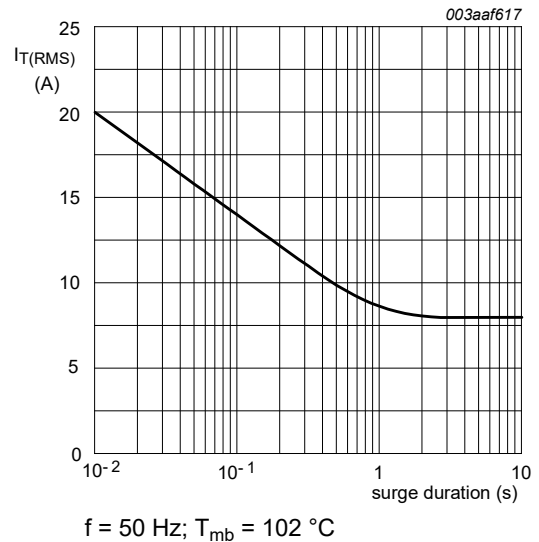
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

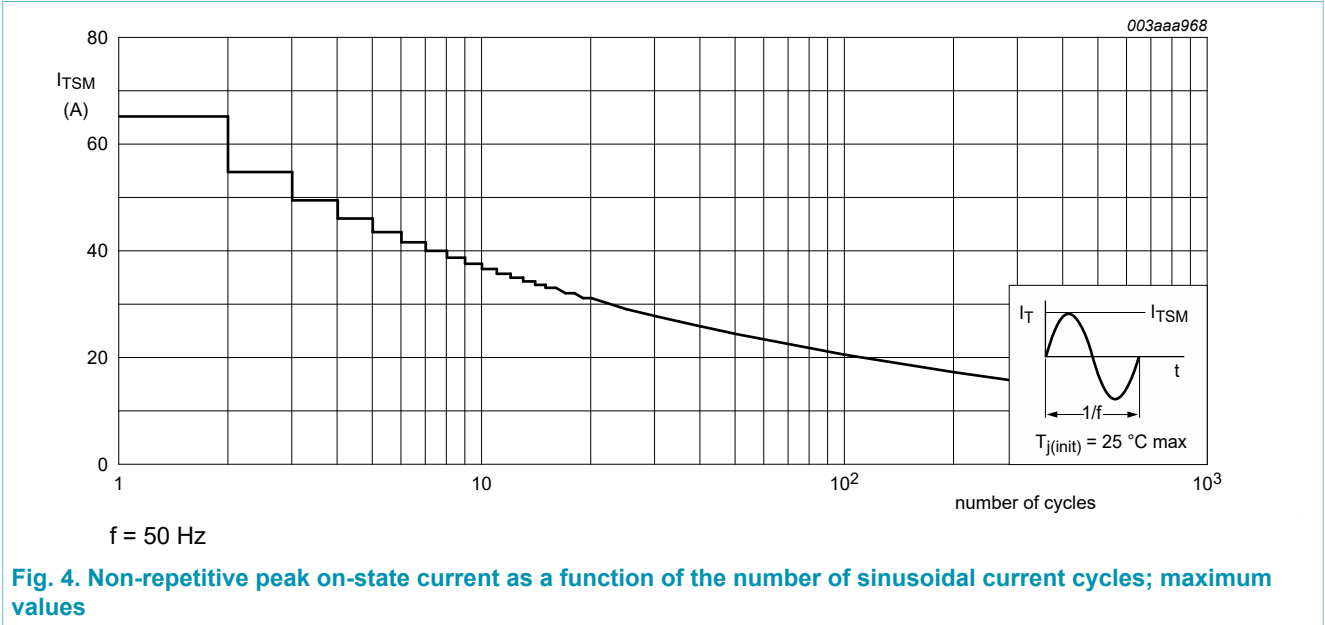
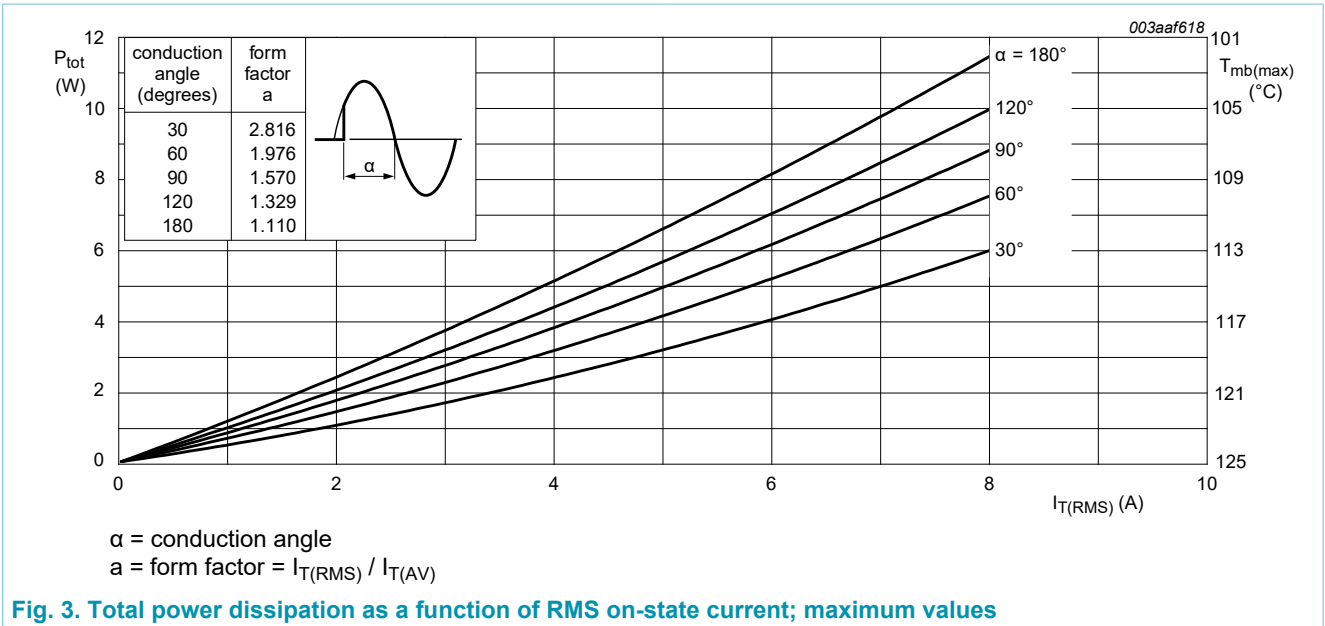
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	1000	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 102\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	8	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	65	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	72	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	21	A <sup>2</sup> s
$di_T/dt$	rate of rise of on-state current	$I_G = 70\text{ mA}$	-	100	A/ $\mu$ s
$I_{GM}$	peak gate current		-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	°C
$T_j$	junction temperature		-	125	°C

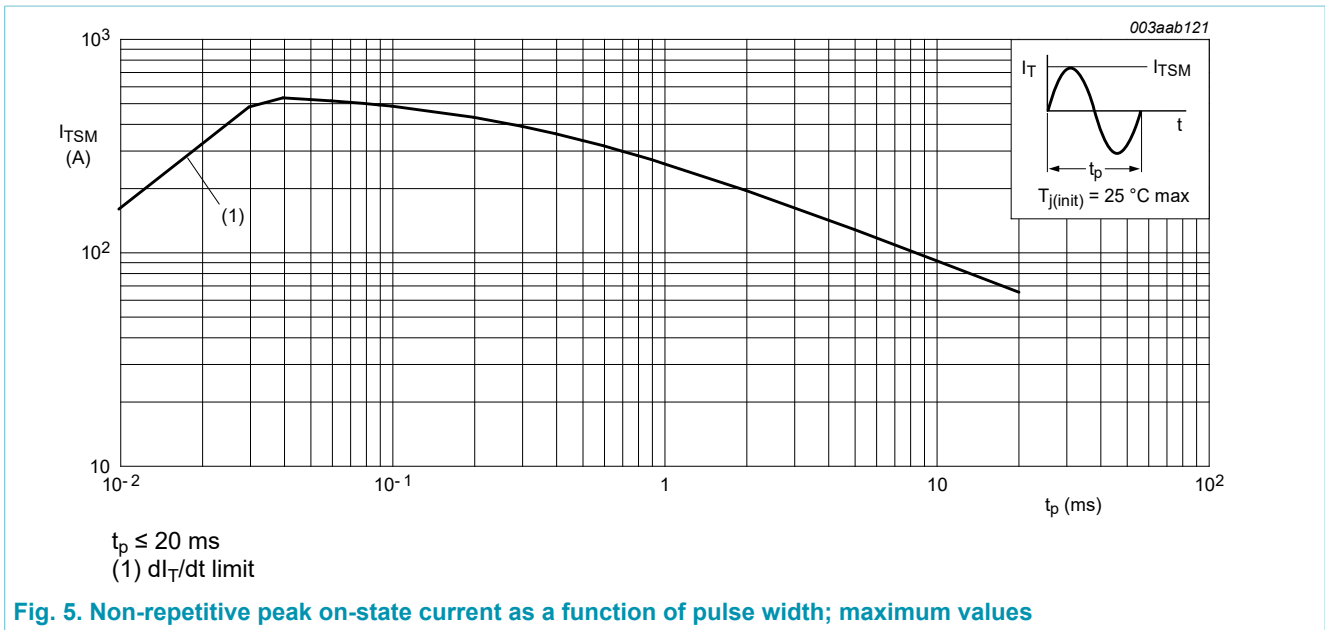


**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



**Fig. 2. RMS on-state current as a function of surge duration; maximum values**





### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	2	K/W
		half cycle; Fig. 6	-	-	2.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	55	-	K/W

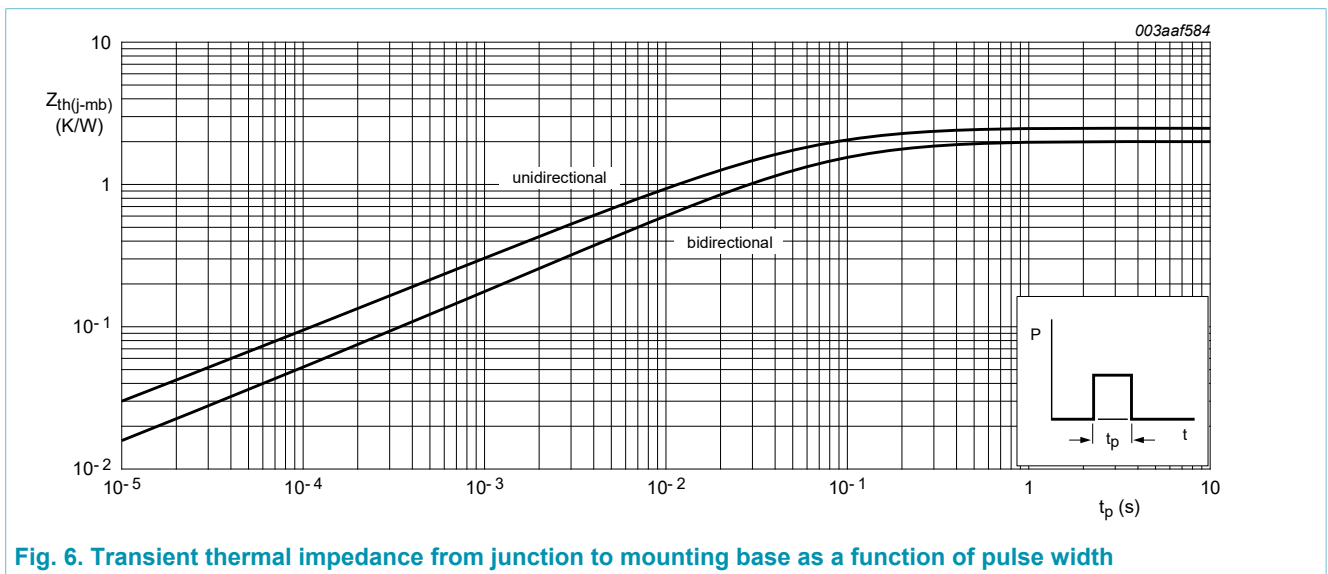
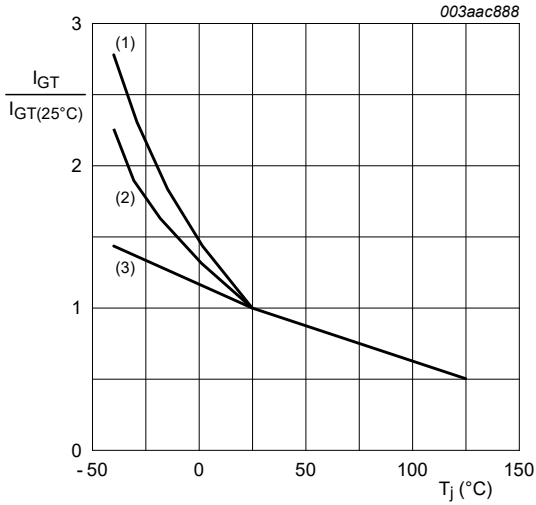


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>	2	6	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>	2	13	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>	2	23	35	mA
I <sub>L</sub>	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	25	50	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	48	75	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	30	50	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>	-	20	50	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>	-	1.3	1.65	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; <a href="#">Fig. 11</a>	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 1000 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
<b>Dynamic characteristics</b>						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 670 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	1000	4000	-	V/μs
dI <sub>com</sub> /dt	rate of change of commutating current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 8 A; dV <sub>com</sub> /dt = 20 V/μs; snubberless condition; gate open circuit; <a href="#">Fig. 12</a>	12	32	-	A/ms
t <sub>gt</sub>	gate-controlled turn-on time	I <sub>TM</sub> = 12 A; V <sub>D</sub> = 1000 V; I <sub>G</sub> = 0.1 A; dI <sub>G</sub> /dt = 5 A/μs	-	2	-	μs



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

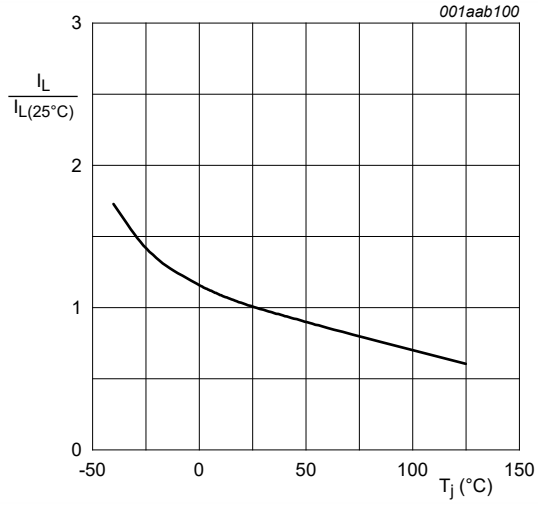


Fig. 8. Normalized latching current as a function of junction temperature

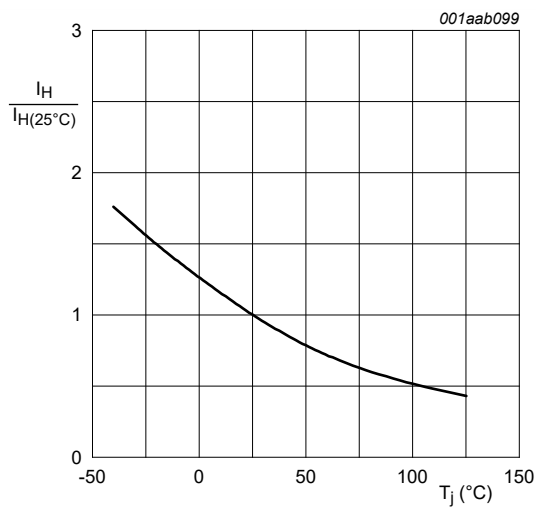
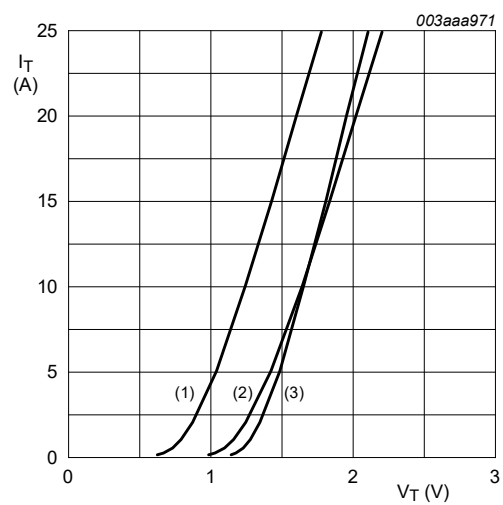


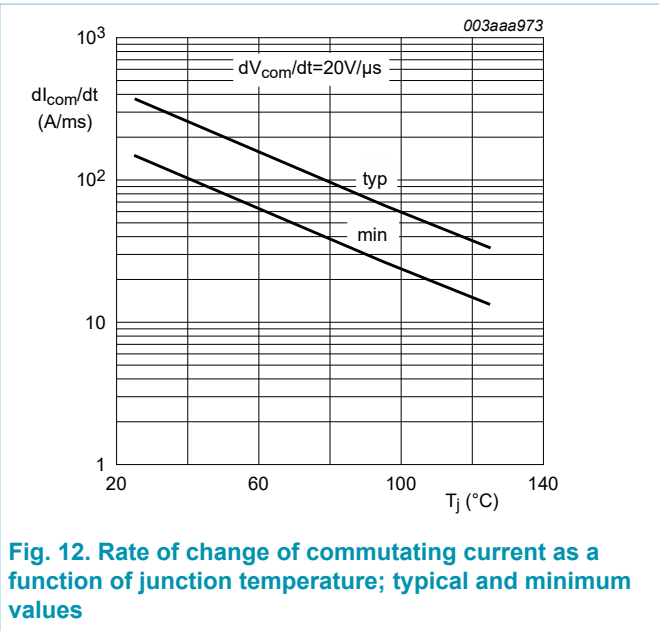
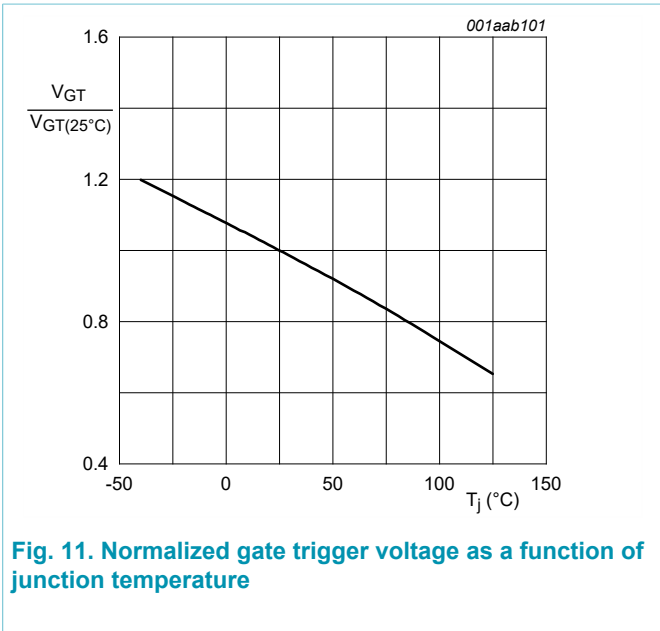
Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.264 V; R_s = 0.0378 \Omega$
- (1)  $T_j = 125^\circ C$ ; typical values
  - (2)  $T_j = 125^\circ C$ ; maximum values
  - (3)  $T_j = 25^\circ C$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage

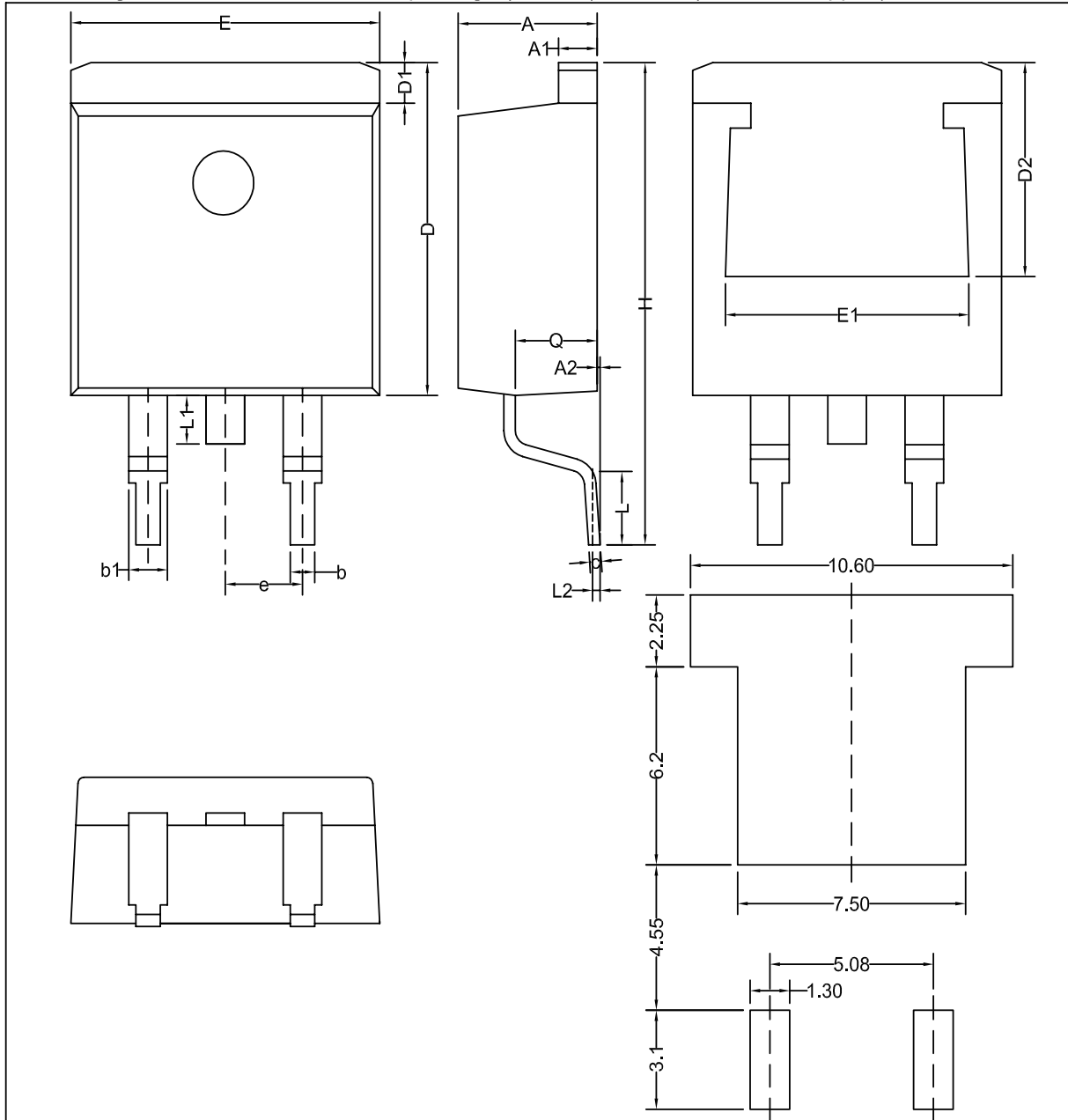




### 11. Package outline

Assembly factory: N

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) TO263

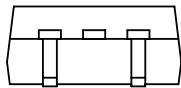
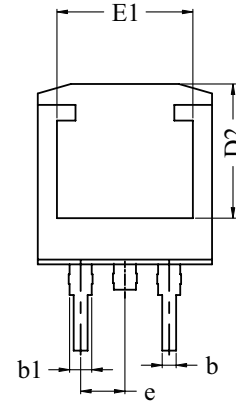
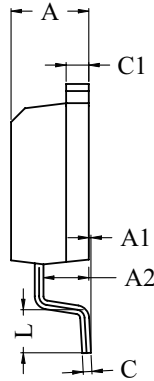
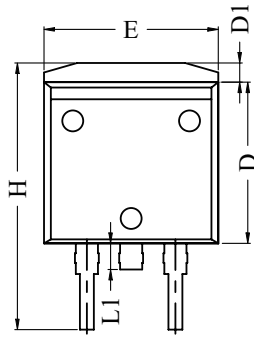


Unit	A	A1	A2	b	b1	c	D	D1	D2	e	E	E1	H	L	L1	L2	Q
min	4.10	1.22	0.00	0.60	1.05	0.34	---	1.20	6.60	2.54 (BSC)	9.70	7.80	14.80	2.10	---	0.25 (BSC)	2.20
max	4.70	1.40	0.25	0.90	1.45	0.64	11.00	1.60	---	---	10.30	---	15.80	2.90	1.75	---	2.79

Assembly factory: P

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

TO263



Dim	All Dimensions in Millimeters		
	Min	Typ	Max
A	4.30	4.46	4.60
A1	0	0.13	0.25
A2	2.50	2.60	2.70
b	0.70	0.80	0.90
b1	1.10	1.27	1.45
C	0.40	0.52	0.60
C1	1.17	1.30	1.40
D	9.10	9.25	9.40
D1	1.00	1.10	1.30
D2	7.40	7.70	8.00
E	9.80	10.00	10.20
E1	7.60	7.80	8.00
e	2.54 BSC		
H	14.80	15.30	15.80
L	2.10	2.47	2.80
L1	1.30	1.50	1.70

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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